PATENT APPLICATION

Sheet 1 of 2

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
10007799-1	
APPLICANT: Xia Sheng et al	
FILING DATE: 04/30/2001	GROUP

jc997 U.S. PTO 09/845845 04/30/01

REFERENCE DESIGNATION — U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1A	6,162,716	12/19/2000	Chen-Hua Yu et al	438	592
	1B	6,136,684	10/24/2000	Nobuhiko Sato et al	438	624
	1C	6,187,604	02/13/2001	Terry L. Gilton	438	20
	1D	5,990,605	11/23/1999	Takamasa Yoshikawa et al	313	310
	1E	5,894,189	04/13/1999	Kiyohide Ogasawara et al	313	310
	1F	5,863,232	01/26/1999	Seok Soo Lee	445	24
	1G	5,556,530	09/17/1996	Walter Finkelstein et al	205	122
	1H	5,296,388	03/22/1994	Shuichi Kameyama et al	437	31
	1I					
	1J					
	1K					

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	TRANSLATION YES	TRANSLATION NO
	1L	EP1047095A2	10/25/2000	Yoshifumi Watabe et al	H01J	1/30	x	
	1M	EP1026721A1	08/09/2000	Takashi Hatai et al	H01J	1/30	x	
	1N	EP1003195A2	05/24/2000	Takashi Hatai et al	H01J	1/30	x	
	1O	EP0913849A2	05/06/1999	Takuya Komoda et al	H01J	1/30	x	
	1P							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	Jean-Claude Vial & Jacques Derrien - "Porous Silicon Science and Technology" - February 1994 pages 32-53
	1R	Selena Chan & Philippe M. Fauchet - "Tunable, Narrow, and Directional Lumiescence From Porous Silicon Light Emitting Devices" - July 1999 - pages 274-276
	1S	Xia Sheng, Hideki Koyama & Nobuyoshi Koshida - "Efficient Surface-Emitting Cold Cathodes Based on Electroluminescent Porous Silicon Diodes" - March/April 1998 - pages 793-795

EXAMINER: [signature]

DATE CONSIDERED: 4/22/03

Rev 10/00 (PTO1449)

FORM PTO-1449

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1A					
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	1C					
	1D					
	1E					
	1F					
	1G					
	1H					
	1I					
	1J					
	1K					

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	TRANSLATION YES	TRANSLATION NO
	1L							
	1M							
	1N							
	1O							
	1P							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	N. Koshida, X. Sheng & T. Komoda - "Quasiballistic Electron Emission From Porous Silicon Diodes" - May 1999 - pages 371-376
	1R	Paul Snow, Yi Zhou, Philip Allcock, John Pottage, Jonathan Knight & Philip Russell - "Porous Silicon" - April 12, 2001 - pages 1-2
	1S	

EXAMINER: [signature] DATE CONSIDERED: 4/22/03

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PTO/SB/08B (08-00)
Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	09/845,945
Filing Date	Apr 30, 2001
First Named Inventor	Poh Boon Phua
Group Art Unit	2874
Examiner Name	
Attorney Docket Number	1085-022-PWH

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		US Patent Application No. 09/963,181 "An Apparatus for Generating Laser Radiation" filed 9/25/01; 18 pages	
		BOWMAN et al; "High Power Diode Pumped Micron Lasers" SPIE Vol. 1865 pp 156 - 163; 1993	
		SHANNON et al; "High Average Power Diode-Pumped Lasers Near 2 um" SPEI Vol. 1865; pp 164-173	
		RUSTAD et al; "Low Threshold Laser-Diode Side-Pumped TM:YAG and TM:Ho:YAG Lasers" IEEE Jnl of Sel Topics in Quatum Electonics Vol 3 2/1997 8 pages	
		HONEA; "115-W TM:YAG Diode-Pumped Solid-State Laser"; IEEE Jnl of Sel Topics in Quatum Electonics Vol 33 9/1997 9 pages	
		JACKSON "Efficient Gain-Switched Operation of a TM-Doped Silica Fiber Laser" EEE Jnl of Sel Topics in Quatum Electron. Vol 3 /1998 11 pages	
		BOLLIG "2-W Ho:YAG Laser Intercavity Pumped by a Diode-Pumped Tm:YAG Laser" Optics Letters Vol 23 No 22 11/1998 3 pages	
✓		RUSTAD; Modeling of Laser-Pumped TM and HO Lasers Accounting for Upconversion and Bround State Depletion; IEEE Journal of Quant. El. V32, #9 9/1996; 12 pages	

Examiner Signature		Date Considered	4/22/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Unique citation designation number. [2] Applicant is to place a check mark here if English language Translation is attached.